

Three Phase Rectifier Bridge

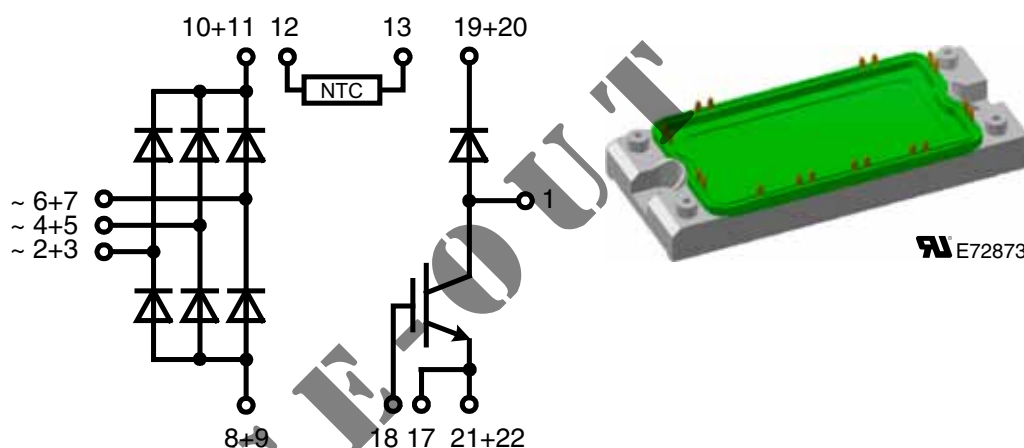
with IGBT and Fast Recovery Diode
for Braking System

Rectifier Diode	Fast Recov. Diode	IGBT
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{dAVM} = 145 \text{ A}$	$V_F = 2.76 \text{ V}$	$I_{C80} = 100 \text{ A}$
$I_{FSM} = 1100 \text{ A}$	$I_{FSM} = 200 \text{ A}$	$V_{CEsat} = 3.7 \text{ V}$

Preliminary data

Part name (Marking on product)

VUB145-16NO1



Features:

- Soldering connections for PCB mounting
- Convenient package outline
- Optional NTC

Application:

- Drive Inverters with brake system

Package:

- Two functions in one package
- Easy to mount with two screws
- Suitable for wave soldering
- High temperature and power cycling capability
- UL registered, E72873

Recommended replacement:

VUB145-16NOXT

IGBT

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			1200	V	
V_{GES}	max. DC gate voltage	continuous	-20		+20	V	
V_{GEM}	max. transient collector gate voltage	transient	-30		+30	V	
I_{C25}	collector current	DC			141	A	
I_{C80}		DC			100	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			570	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 150\text{ A}; V_{GE} = 15\text{ V}$			3.7	V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 3\text{ mA}$	4.5		6.45	V	
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$ $V_{CE} = 0.8 \cdot V_{CES}; V_{GE} = 0\text{ V}$			0.1 0.5	mA mA	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			5.7	nF	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 720\text{ V}; I_C = 75\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega; L = 100\ \mu\text{H}$			80	ns	
$t_{d(off)}$	turn-off delay time		$T_{VJ} = 125^{\circ}\text{C}$			680	ns
E_{on}	turn-on energy per pulse					9	mJ
E_{off}	turn-off energy per pulse					7.5	mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega; L = 100\ \mu\text{H}$			150	A	
V_{CEK}	clamped inductive load;	$T_{VJ} = 125^{\circ}\text{C}$			$\leq V_{CES} - L_S \cdot di/dt$	V	
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 15\ \Omega;$ non-repetitive			10	μs	
RBSOA	reverse bias safe operating area	$V_{CE} = 1200\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 15\ \Omega; L = 100\ \mu\text{H};$ clamped inductive load			150	A	
R_{thJC}	thermal resistance junction to case				0.22	K/W	
R_{thCH}	thermal resistance case to heatsink				0.22	K/W	

Fast Recovery Diode

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			1200	V	
I_{FAV}	average forward current	rect.; $d = 0.5$			27	A	
I_{FRMS}	rms forward current	rect.; $d = 0.5$			38	A	
I_{FSM}	max. surge forward current	$t = 10\text{ ms}$			200	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			130	W	
V_{F0}	threshold voltage	$T_{VJ} = 150^{\circ}\text{C}$			1.3	V	
r_F	slope resistance	for power loss calculation only			16	m Ω	
V_F	forward voltage	$I_F = 30\text{ A}$			2.76	V	
I_R	reverse current	$V_R = V_{RRM}$			0.25	mA	
		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			1	mA	
I_{RM}	reverse recovery current	$I_F = 50\text{ A}; V_R = 100\text{ V}; di_F/dt = -100\text{ A}/\mu\text{s}$			5.5	11	A
t_{rr}	reverse recovery time	$I_F = 1\text{ A}; V_R = 30\text{ V}; di_F/dt = -200\text{ A}/\mu\text{s}$			40	ns	
R_{thJC}	thermal resistance junction to case				0.9	K/W	
R_{thCH}	thermal resistance case to heatsink				0.1	K/W	

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Rectifier Diode

Symbol	Conditions		Ratings			
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$		1600	V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		0.1 2	mA mA
V_F	forward voltage	$I_F = 150\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.68	V
$I_{D(AV)M}$	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^{\circ}\text{C}$		145	A
V_{F0}	threshold voltage		$T_{VJ} = 150^{\circ}\text{C}$		0.85	V
r_F	slope resistance	for power loss calculation only			5.9	m Ω
R_{thJC}	thermal resistance junction to case	per diode	$T_{VJ} = 25^{\circ}\text{C}$		0.5	K/W
R_{thCH}	thermal resistance case to heatsink		$T_{VJ} = 25^{\circ}\text{C}$		0.1	K/W
P_{tot}	total power dissipation		$T_{VJ} = 25^{\circ}\text{C}$		250	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms (50Hz)}$ $V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		1100 960	A A
I^2t	value for fusing	$t = 10\text{ ms (50Hz)}$ $V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$		6050 4610	A ² s A ² s

Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
R_{25}	resistance		$T_C = 25^{\circ}\text{C}$	4.75	5.0	5.25	k Ω
$B_{25/85}$					3375		K

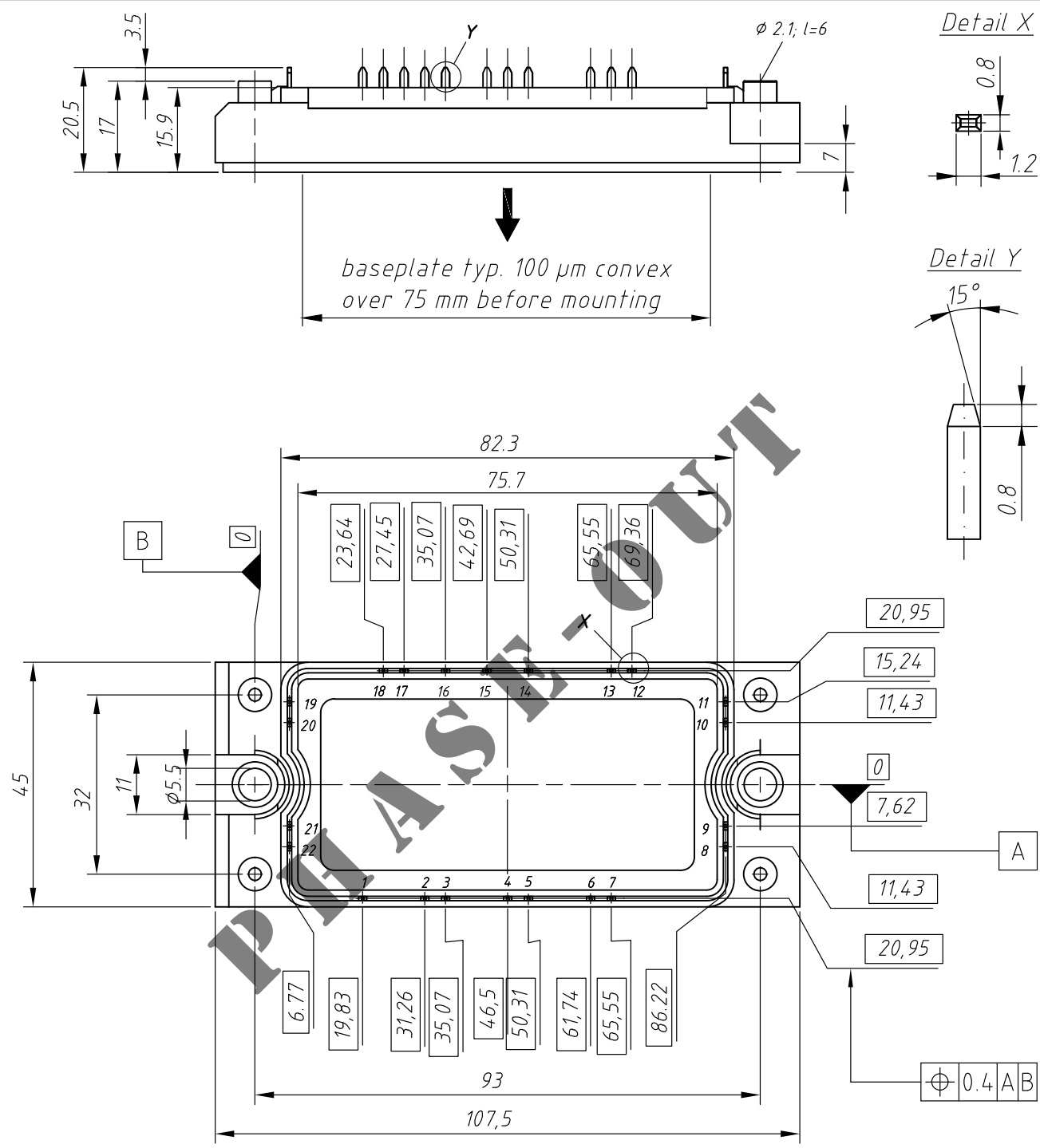
Module

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	$^{\circ}\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^{\circ}\text{C}$
T_{stg}	storage temperature		-40		125	$^{\circ}\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz};$			2500 3000	V~ V~
M_d	mounting torque	(M5)	2.7		3.3	Nm
d_s	creep distance on surface		12.7			mm
d_A	strike distance through air		9.6			mm
a	maximum allowable acceleration		50			m/s ²
$R_{pin-chip}$	thermal resistance pin to chip		$T_{VJ} = 25^{\circ}\text{C}$	2		m Ω
Weight				180		g

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

IXYS **VUB 145-16NO1**

Outline Drawing **Dimensions in mm (1 mm = 0.0394")**



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	VUB 145-16NO1	VUB145-16NO1	Box	6	496669

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IXYS **VUB 145-16NO1**

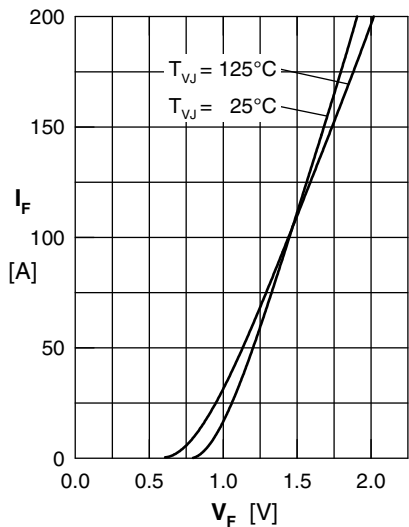


Fig. 1 Forward current vs. voltage drop per diode

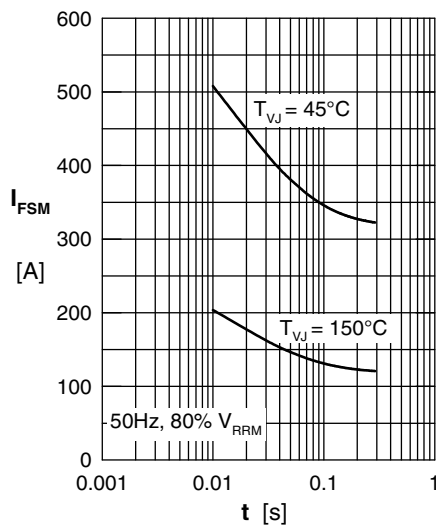


Fig. 2 Surge overload current

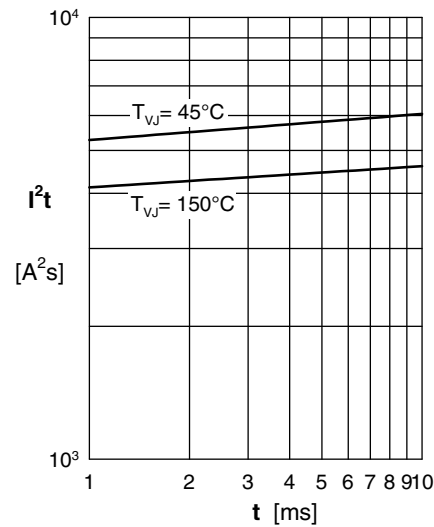


Fig. 3 I²t versus time per diode

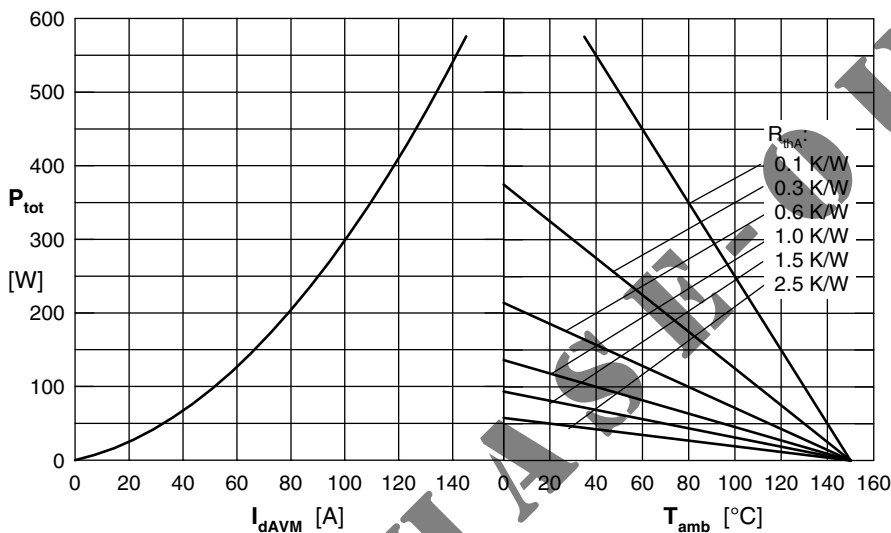


Fig. 4 Power dissipation versus direct output current and ambient temperature, sine 180°

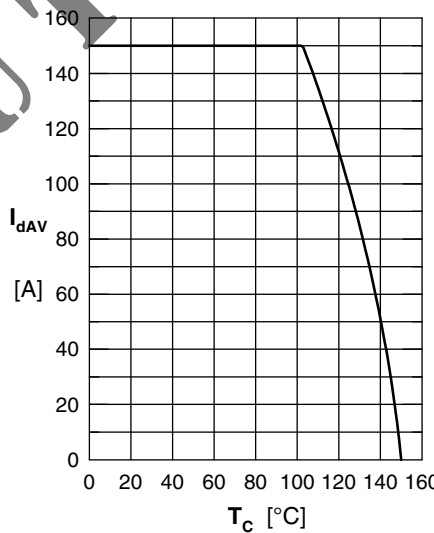


Fig. 5 Max. forward current vs. case temperature

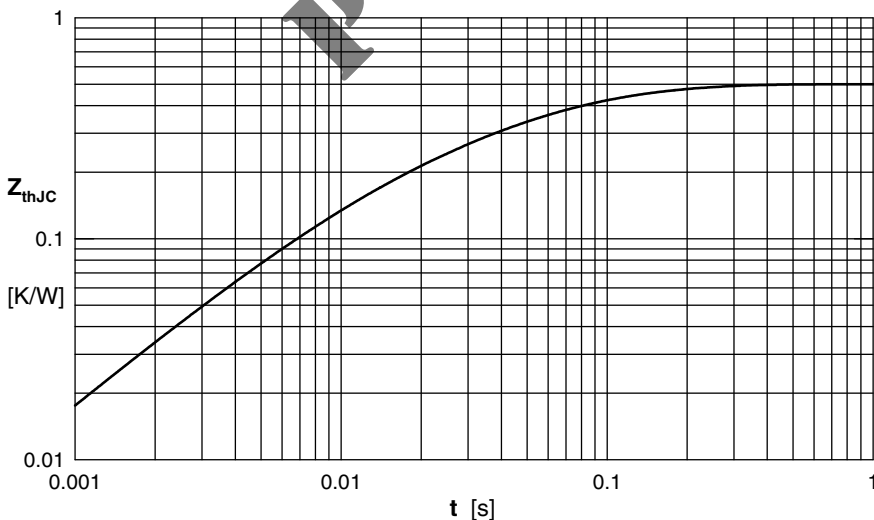


Fig. 6 Transient thermal impedance junction to case

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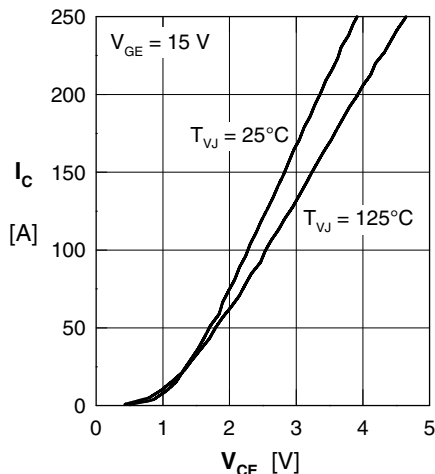


Fig. 7 Typ. output characteristics

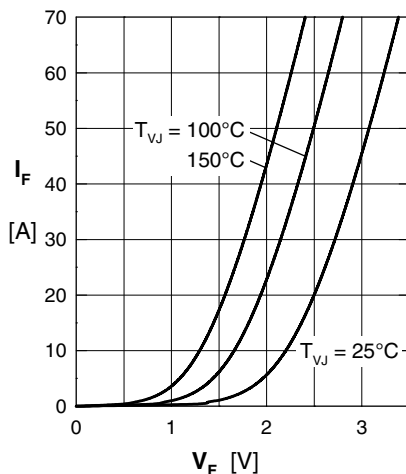


Fig. 8 Typ. forward characteristics of free wheeling diode

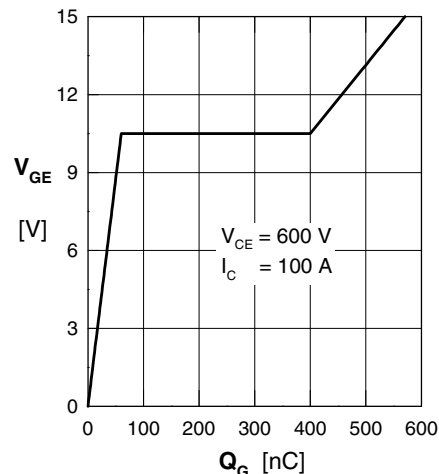


Fig. 9 Typ. turn on gate charge

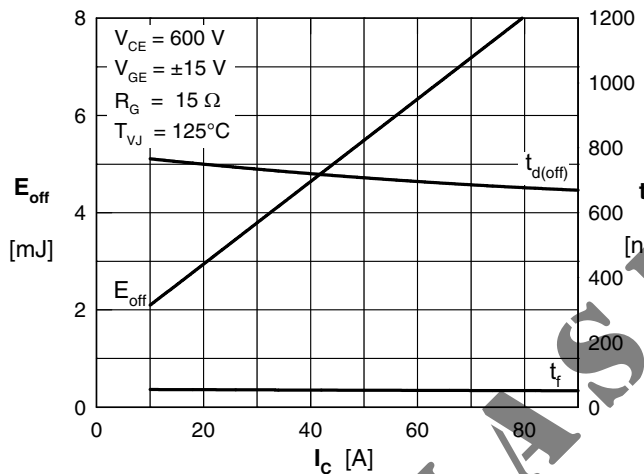


Fig. 10 Typ. turn off energy and switching times versus collector current

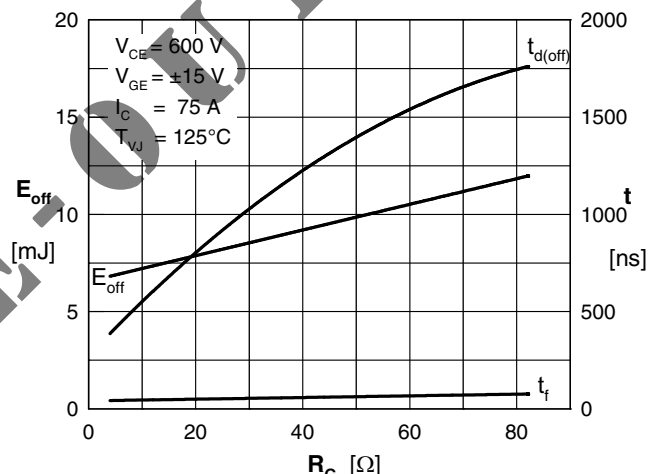


Fig. 11 Typ. turn off energy and switching times versus gate resistor

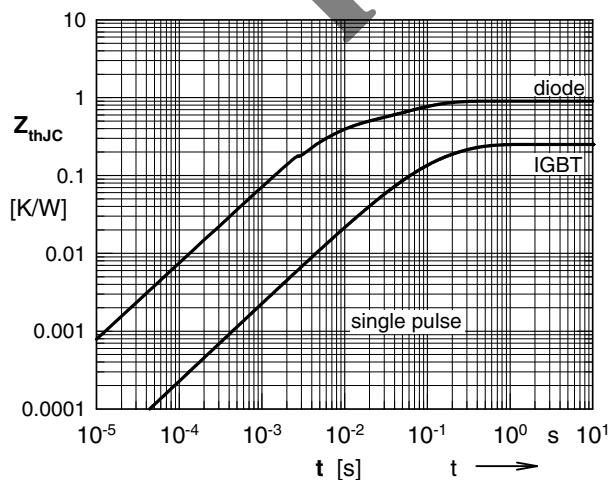


Fig. 12 Typ. transient thermal impedance

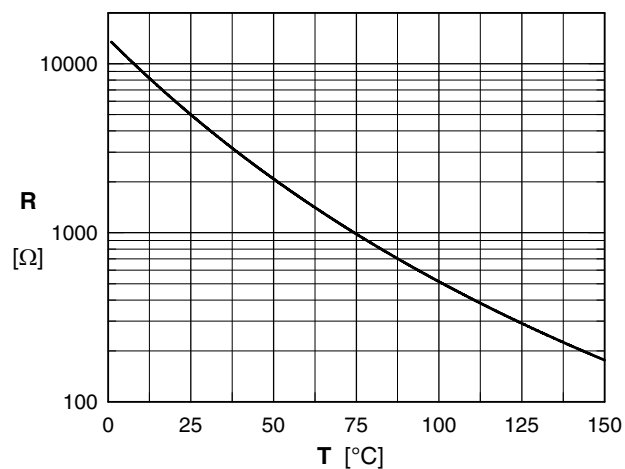


Fig. 13 Typ. thermistor resistance vs. temperature

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